



APTM50SKM19G Information

Heisener.com

Part Number APTM50SKM19G Manufacturer Microsemi Corporation

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 500V 163A SP6

Package SP6

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



Request a Quote

Certified Quality

For Reference Only

Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.









APTM50SKM19G Specifications

Manufacturer Part NumberAPTM50SKM19GManufacturerMicrosemi CorporationCategoryDiscrete Semiconductor ProductsTransistors - FETs, MOSFETs - SinglePackageSP6Series-FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)500VCurrent - Continuous Drain (Id) @ 25°C163ADrive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 10mAGate Charge (Qg) (Max) @ Vgs492nC @ 10VInput Capacitance (Ciss) (Max) @ Vds22400pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)1136W (Tc)Rds On (Max) @ Id, Vgs22.5 mOhm @ 81.5A, 10VOperating Temperature-40°C ~ 150°C (TJ)Mounting TypeChassis Mount		
Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single SP6 Series FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 163A Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Questian Temperature Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single SP6 SP6 SP6 SP6 N-Channel NOSFET (Metal Oxide) 500V 163A 10V 5V @ 10mA 492nC @ 10V 10PU 10P	Manufacturer Part Number	APTM50SKM19G
Package SP6 Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 500V Current - Continuous Drain (Id) @ 25°C 163A Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 5V @ 10mA Gate Charge (Qg) (Max) @ Vgs 492nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 22400pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 1136W (Tc) Rds On (Max) @ Id, Vgs 22.5 mOhm @ 81.5A, 10V Operating Temperature -40°C ~ 150°C (TJ)	Manufacturer	Microsemi Corporation
Package SP6 Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 500V Current - Continuous Drain (Id) @ 25°C 163A Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 5V @ 10mA Gate Charge (Qg) (Max) @ Vgs 492nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 22400pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 1136W (Tc) Rds On (Max) @ Id, Vgs 22.5 mOhm @ 81.5A, 10V Operating Temperature -40°C ~ 150°C (TJ)	Category	Discrete Semiconductor Products
Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 500V Current - Continuous Drain (Id) @ 25°C 163A Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 5V @ 10mA Gate Charge (Qg) (Max) @ Vgs 492nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 22400pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 1136W (Tc) Rds On (Max) @ Id, Vgs 22.5 mOhm @ 81.5A, 10V Operating Temperature -40°C ~ 150°C (TJ)		Transistors - FETs, MOSFETs - Single
FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 500V Current - Continuous Drain (Id) @ 25°C 163A Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 5V @ 10mA Gate Charge (Qg) (Max) @ Vgs 492nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 22400pF @ 25V Vgs (Max) ±30V FET Feature Power Dissipation (Max) 1136W (Tc) Rds On (Max) @ Id, Vgs 22.5 mOhm @ 81.5A, 10V Operating Temperature -40°C ~ 150°C (TJ)	Package	SP6
Technology Drain to Source Voltage (Vdss) 500V Current - Continuous Drain (Id) @ 25°C 163A Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 5V @ 10mA Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 22400pF @ 25V Vgs (Max) FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature -MOSFET (Metal Oxide) 500V 163A 10V 25V @ 10mA 492nC @ 10V 22400pF @ 25V 22400pF @ 25V 225 mOhm @ 81.5A, 10V -40°C ~ 150°C (TJ)	Series	-
Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 163A Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature 500V 163A 10V 5V @ 10mA 492nC @ 10V 22400pF @ 25V 230V 492nC @ 10V 1136W (Tc) 225 mOhm @ 81.5A, 10V -40°C ~ 150°C (TJ)	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C 163A Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 5V @ 10mA Gate Charge (Qg) (Max) @ Vgs 492nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 22400pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 1136W (Tc) Rds On (Max) @ Id, Vgs 22.5 mOhm @ 81.5A, 10V Operating Temperature -40°C ~ 150°C (TJ)	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 5V @ 10mA Gate Charge (Qg) (Max) @ Vgs 492nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 22400pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 1136W (Tc) Rds On (Max) @ Id, Vgs 22.5 mOhm @ 81.5A, 10V Operating Temperature -40°C ~ 150°C (TJ)	Drain to Source Voltage (Vdss)	500V
Vgs(th) (Max) @ Id 5V @ 10mA Gate Charge (Qg) (Max) @ Vgs 492nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 22400pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 1136W (Tc) Rds On (Max) @ Id, Vgs 22.5 mOhm @ 81.5A, 10V Operating Temperature -40°C ~ 150°C (TJ)	Current - Continuous Drain (Id) @ 25°C	163A
Gate Charge (Qg) (Max) @ Vgs 492nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 22400pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 1136W (Tc) Rds On (Max) @ Id, Vgs 22.5 mOhm @ 81.5A, 10V Operating Temperature -40°C ~ 150°C (TJ)	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds 22400pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 1136W (Tc) Rds On (Max) @ Id, Vgs 22.5 mOhm @ 81.5A, 10V Operating Temperature -40°C ~ 150°C (TJ)	Vgs(th) (Max) @ Id	5V @ 10mA
Vgs (Max) $\pm 30 \text{V}$ FET Feature-Power Dissipation (Max) 1136W (Tc) Rds On (Max) @ Id, Vgs $22.5 \text{ mOhm @ } 81.5 \text{A}, 10 \text{V}$ Operating Temperature $-40^{\circ}\text{C} \sim 150^{\circ}\text{C (TJ)}$	Gate Charge (Qg) (Max) @ Vgs	492nC @ 10V
FET Feature - Power Dissipation (Max) 1136W (Tc) Rds On (Max) @ Id, Vgs 22.5 mOhm @ 81.5A, 10V Operating Temperature -40°C ~ 150°C (TJ)	Input Capacitance (Ciss) (Max) @ Vds	22400pF @ 25V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 22.5 mOhm @ 81.5A, 10V Operating Temperature -40°C ~ 150°C (TJ)	Vgs (Max)	±30V
Rds On (Max) @ Id, Vgs 22.5 mOhm @ 81.5A, 10V Operating Temperature -40°C ~ 150°C (TJ)	FET Feature	-
Operating Temperature $-40^{\circ}\text{C} \sim 150^{\circ}\text{C} \text{ (TJ)}$	Power Dissipation (Max)	1136W (Tc)
	Rds On (Max) @ Id, Vgs	22.5 mOhm @ 81.5A, 10V
Mounting Type Chassis Mount	Operating Temperature	-40°C ~ 150°C (TJ)
Chaosis Would	Mounting Type	Chassis Mount
Supplier Device Package SP6	Supplier Device Package	SP6
Package / Case SP6	Package / Case	SP6
Report errors?		Report errors?

APTM50SKM19G Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

APTM50SKM19G Payment Methods



















APTM50SKM19G Shipping Methods













If you have any question about APTM50SKM19G, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com